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[CQY37N](#)

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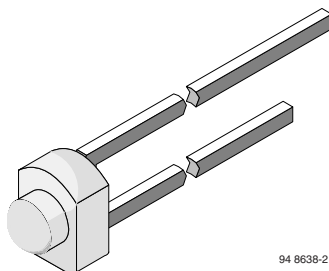
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**CQY37N**

Vishay Semiconductors

## Infrared Emitting Diode, 950 nm, GaAs



94 8638-2

### FEATURES

- Package type: leaded
- Package form: T-¾
- Dimensions (in mm): Ø 1.8
- Peak wavelength:  $\lambda_p = 950$  nm
- High reliability
- Angle of half intensity:  $\phi = \pm 12^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Package matches with detector BPW17N
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### DESCRIPTION

CQY37N is an infrared, 950 nm emitting diode in GaAs technology molded in a miniature, clear plastic package with lens.

### APPLICATIONS

- Radiation source in near infrared range

### PRODUCT SUMMARY

| COMPONENT | $I_e$ (mW/sr) | $\phi$ (deg) | $\lambda_p$ (nm) | $t_r$ (ns) |
|-----------|---------------|--------------|------------------|------------|
| CQY37N    | 5             | $\pm 12$     | 950              | 800        |

#### Note

- Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS                      | PACKAGE FORM |
|---------------|-----------|------------------------------|--------------|
| CQY37N        | Bulk      | MOQ: 5000 pcs, 5000 pcs/bulk | T-¾          |

#### Note

- MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ\text{C}$ , unless otherwise specified)

| PARAMETER                           | TEST CONDITION             | SYMBOL     | VALUE         | UNIT             |
|-------------------------------------|----------------------------|------------|---------------|------------------|
| Reverse voltage                     |                            | $V_R$      | 5             | V                |
| Forward current                     |                            | $I_F$      | 100           | mA               |
| Surge forward current               | $t_p \leq 100 \mu\text{s}$ | $I_{FSM}$  | 2             | A                |
| Power dissipation                   |                            | $P_V$      | 160           | mW               |
| Junction temperature                |                            | $T_j$      | 100           | $^\circ\text{C}$ |
| Operating temperature range         |                            | $T_{amb}$  | - 25 to + 85  | $^\circ\text{C}$ |
| Storage temperature range           |                            | $T_{stg}$  | - 25 to + 100 | $^\circ\text{C}$ |
| Soldering temperature               | $t \leq 3$ s               | $T_{sd}$   | 245           | $^\circ\text{C}$ |
| Thermal resistance junction/ambient | Leads not soldered         | $R_{thJA}$ | 450           | K/W              |

## CQY37N

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GaAs

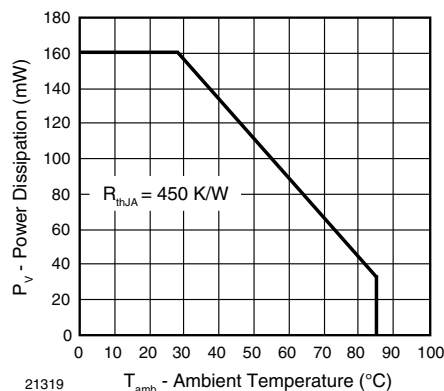


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

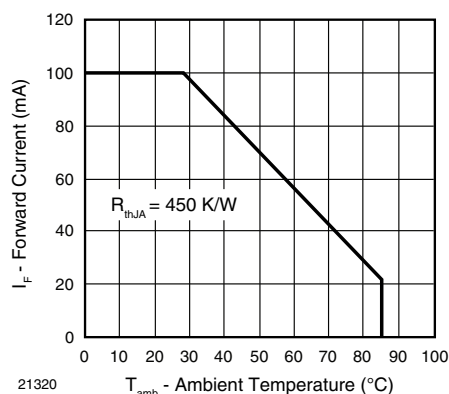


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS ( $T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified) |                                                                          |                 |      |          |      |               |
|--------------------------------------------------------------------------------------|--------------------------------------------------------------------------|-----------------|------|----------|------|---------------|
| PARAMETER                                                                            | TEST CONDITION                                                           | SYMBOL          | MIN. | TYP.     | MAX. | UNIT          |
| Forward voltage                                                                      | $I_F = 50\text{ mA}$ , $t_p \leq 20\text{ ms}$                           | $V_F$           |      | 1.3      | 1.6  | V             |
| Temperature coefficient of $V_F$                                                     | $I_F = 100\text{ mA}$                                                    | $TK_{VF}$       |      | - 1.3    |      | mV/K          |
| Breakdown voltage                                                                    | $I_R = 100\text{ }\mu\text{A}$                                           | $V_{(BR)}$      | 5    |          |      | $\mu\text{A}$ |
| Junction capacitance                                                                 | $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$                        | $C_j$           |      | 50       |      | pF            |
| Radiant intensity                                                                    | $I_F = 50\text{ mA}$ , $t_p \leq 20\text{ ms}$                           | $I_e$           | 2.2  | 5        | 11   | mW/sr         |
| Radiant power                                                                        | $I_F = 50\text{ mA}$ , $t_p \leq 20\text{ ms}$                           | $\phi_e$        | 4.8  | 10       | 17.8 | mW            |
| Temperature coefficient of $\phi_e$                                                  | $I_F = 50\text{ mA}$                                                     | $TK_{\phi_e}$   |      | - 0.8    |      | %/K           |
| Angle of half intensity                                                              |                                                                          | $\phi$          |      | $\pm 12$ |      | deg           |
| Peak wavelength                                                                      | $I_F = 50\text{ mA}$                                                     | $\lambda_p$     |      | 950      |      | nm            |
| Spectral bandwidth                                                                   | $I_F = 50\text{ mA}$                                                     | $\Delta\lambda$ |      | 50       |      | nm            |
| Rise time                                                                            | $I_F = 100\text{ mA}$                                                    | $t_r$           |      | 800      |      | ns            |
|                                                                                      | $I_F = 1.5\text{ A}$ , $t_p/T = 0.01$ , $t_p \leq 10\text{ }\mu\text{s}$ | $t_r$           |      | 400      |      | ns            |
| Virtual source diameter                                                              |                                                                          | $d$             |      | 1.2      |      | mm            |

### BASIC CHARACTERISTICS ( $T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified)

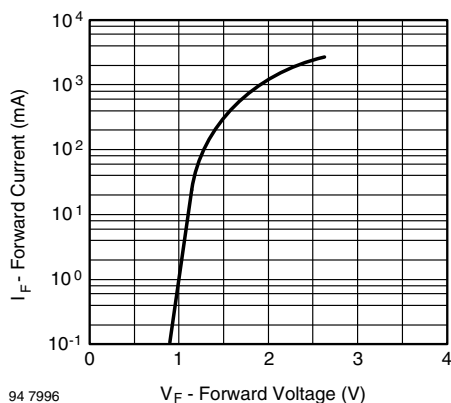


Fig. 3 - Forward Current vs. Forward Voltage

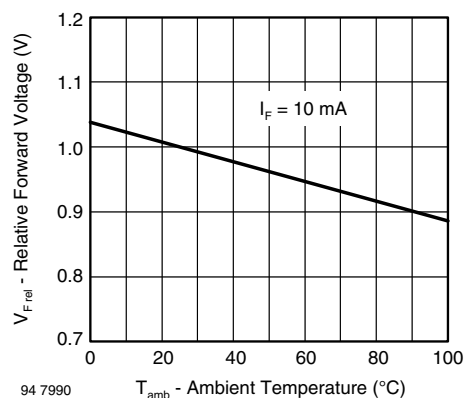


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature



## CQY37N

Infrared Emitting Diode, 950 nm, GaAs Vishay Semiconductors

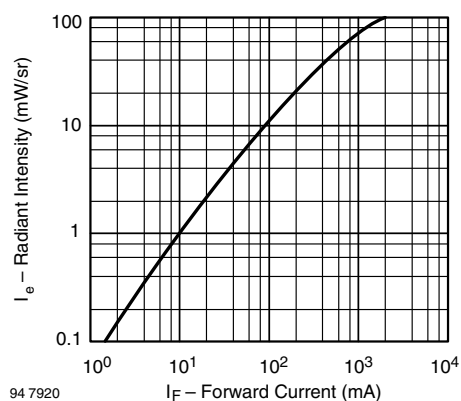


Fig. 5 - Radiant Intensity vs. Forward Current

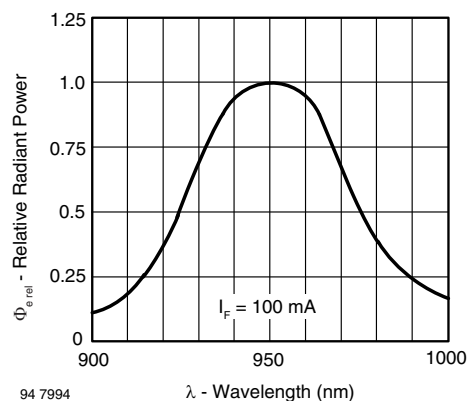


Fig. 8 - Relative Radiant Power vs. Wavelength

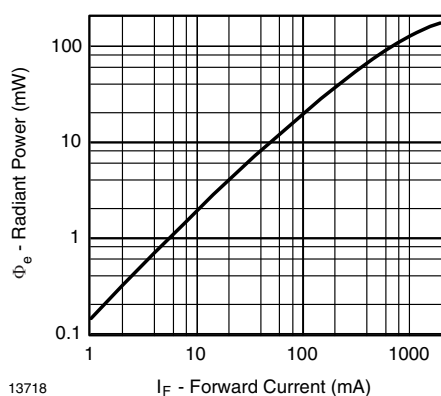


Fig. 6 - Radiant Power vs. Forward Current

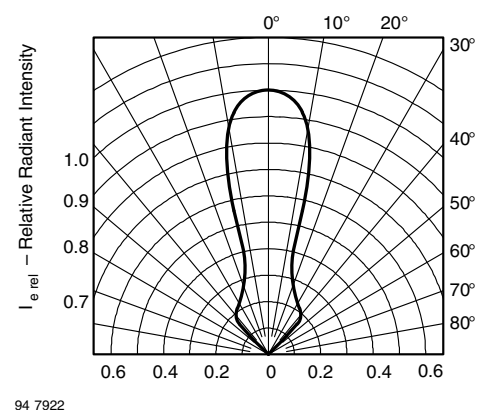


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

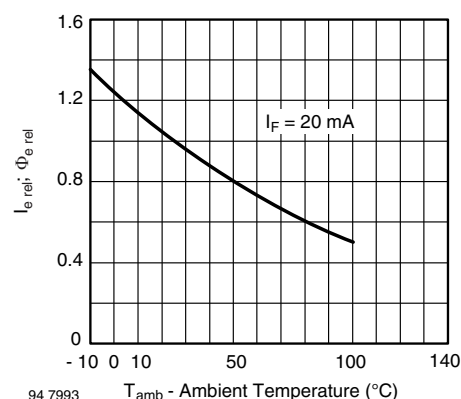


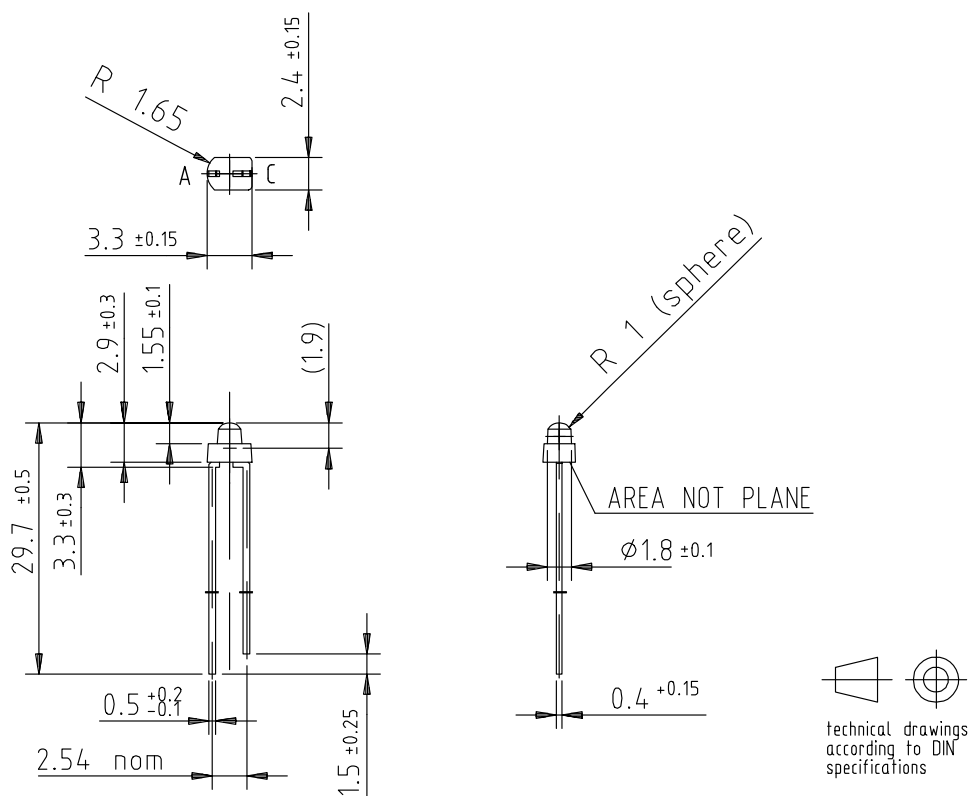
Fig. 7 - Relative Radiant Intensity/Power vs. Ambient Temperature

## CQY37N

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### PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5052.01-4  
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95 11262



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